

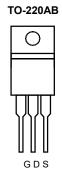
K3418-VB Datasheet N-Channel 60 V (D-S) MOSFET

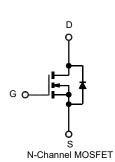
PRODUCT SUMMARY				
V _{DS}	60	V		
R _{DS(on)} V _{GS} = 10 V	5	mΩ		
I _D	120	Α		
Configuration	Single			

FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET
- Material categorization:







ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
Parameter		Symbol	Limit	Unit			
Gate-Source Voltage		V _{GS}	± 20	V			
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	I-	120				
	T _C = 100 °C	l _D	90				
Pulsed Drain Current		I _{DM}	350	A			
Continuous Source Current (Diode Conduction)		I _S	70ª				
Avalanche Current	anche Current		50				
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ			
Maximum Power Dissipation	T _C = 25 °C	P _D	136	W			
	T _A = 25 °C	'B	3 ^b , 8.3 ^{b, c}	l vv			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Marriago los ations to Anglianda	t ≤ 10 sec	R _{thJA}	15	18			
Maximum Junction-to-Ambient ^a	Steady State		40	50	°C/W		
Maximum Junction-to-Case		R _{thJC}	0.85	1.1			

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t \le 10 \text{ s}$.



Parameter	er Symbol Test Conditions Min.		Min.	Typ.a	Max.	Unit
Static			l			
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA 60				V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = 60 V, V _{GS} = 0 V			1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C	/ _{GS} = 0 V, T _J = 175 °C		250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	60			Α
Drain-Source On-State Resistance ^b		V _{GS} = 10 V, I _D = 20 A		5		
	_D	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		10		mΩ
	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		15		
		V _{GS} = 7.5 V, I _D = 15 A		8		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S
Dynamic			<u>'</u>	'	'	
Input Capacitance	C _{iss}			6800		
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		570		pF
Reverse Transfer Capacitance	C _{rss}			325		
Total Gate Charge ^c	Qg			47	70	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		10		nC
Gate-Drain Charge ^c	Q_{gd}			12		
Turn-On Delay Time ^c	t _{d(on)}			10	20	
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, R_{L} = 0.6 \Omega$		15	25	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50$ A, V_{GEN} = 10 V, R_g = 2.5 Ω		35	50	ns
Fall Time ^c	t _f			20	30	
Source-Drain Diode Ratings and Ch	aracteristics (T _C = 25 °C)	•		· '	
Pulsed Current	I _{SM}			350		Α
Diode Forward Voltage	V _{SD}	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns

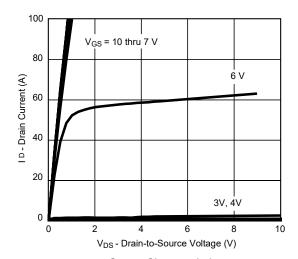
Notes:

- a. For design aid only; not subject to production testing. b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. Independent of operating temperature.

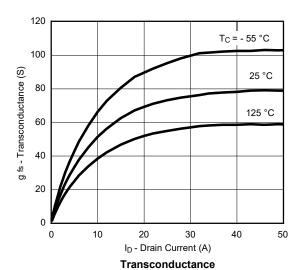
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics

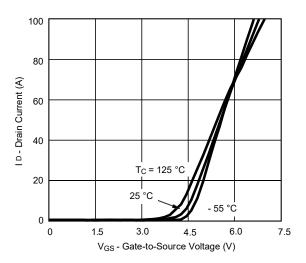


C - Capacitance (pF) 2000 2000 2000 2000 2000 2000 C_{oss} 1000 C_{rss}

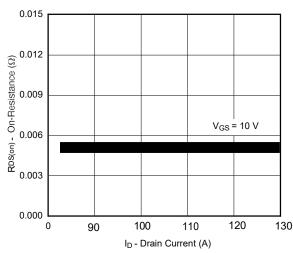
20

 C_{iss}

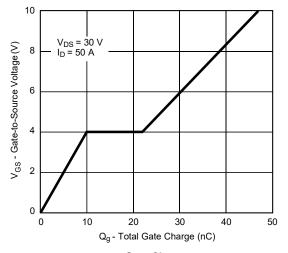
V_{DS} - Drain-to-Source Voltage (V) Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

8000

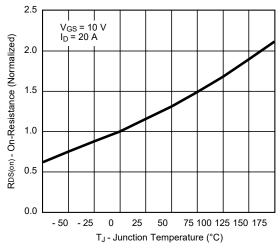
7000

6000

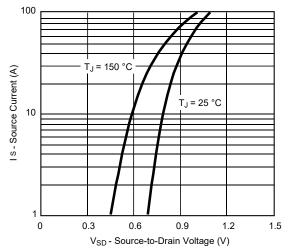
0 0



TYPICAL CHARACTERISTICS (25 °C unless noted)



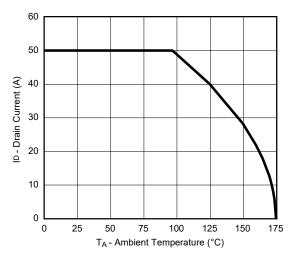
On-Resistance vs. Junction Temperature



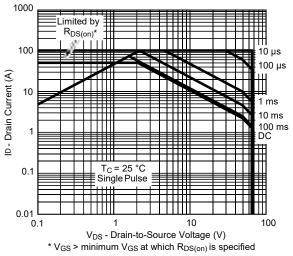
Source-Drain Diode Forward Voltage



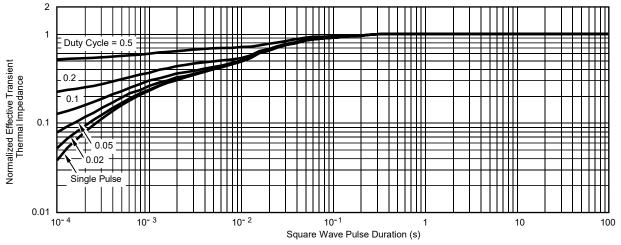
THERMAL RATINGS



Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



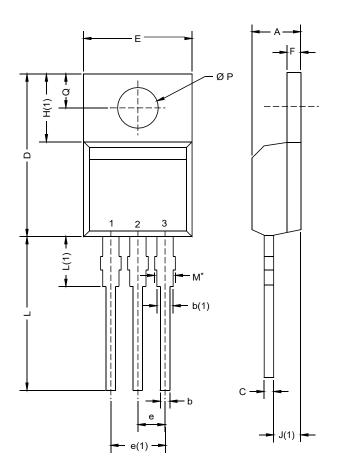
Normalized Thermal Transient Impedance, Junction-to-Case

服务热线:400-655-8788

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TO-220AB



	MILLIMETERS		INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	4.25	4.65	0.167	0.183		
b	0.69	1.01	0.027	0.040		
b(1)	1.20	1.73	0.047	0.068		
С	0.36	0.61	0.014	0.024		
D	14.85	15.49	0.585	0.610		
E	10.04	10.51	0.395	0.414		
е	2.41	2.67	0.095	0.105		
e(1)	4.88	5.28	0.192	0.208		
F	1.14	1.40	0.045	0.055		
H(1)	6.09	6.48	0.240	0.255		
J(1)	2.41	2.92	0.095	0.115		
L	13.35	14.02	0.526	0.552		
L(1)	3.32	3.82	0.131	0.150		
ØΡ	3.54	3.94	0.139	0.155		
Q	2.60	3.00	0.102	0.118		
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471						

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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